

AMENDMENTS TO THE SPECIFICATION:

Please replace the paragraph bridging page 10 and page 11 with the following amended paragraph:

FIG. 4 shows a thickness of each layer in a polymeric optical device (AWG) being fabricated according to a preferred embodiment of the present invention. Referring to FIG. 4, the lower cladding layer 12 having a thickness of 11 μm is formed on the silicon substrate 10 (~~referring to FIG. 2E~~), the core layer pattern 14a of about 6x6 μm is formed on the lower cladding layer 12, and the upper cladding layer 18 having a thickness of about 16 μm or more is formed on the lower cladding layer 12 in which the core layer pattern 14 is formed. At this time, the core layer pattern 14a of 6x6 μm is formed by forming the core layer 14 having a thickness of 6 μm on the lower cladding layer 16 and then etching it by a thickness of about 7 μm into a shape of the etching mask, which is formed by means of the photolithography method, as described above. Here, the thickness of the core layer 14 is 6 μm , but the etched depth of the core layer 14 is 7 μm . It means that the lower cladding layer 12 is over-etched by about 1 μm .

Please replace the second full paragraph on page 6 with the following amended paragraph:

FIGs. 2A to ~~2E~~ 2D are cross sectional views of processes, respectively, for explaining a method for fabricating the polymeric

optical device of FIG. 1.